

U.S. Patent Application Serial No. 10/665,204  
Response filed July 15, 2005  
Reply to OA dated March 23, 2005

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (Original): A semiconductor light-receiving device comprising:

a semi-insulating substrate;

a semiconductor layer of a first conduction type that is formed on the semi-insulating substrate;

a buffer layer of the first conduction type that is formed on the semi-insulating substrate and has a lower impurity concentration than the semiconductor layer of the first conduction type;

a light absorption layer that is formed on the buffer layer and generates carriers in accordance with incident light;

a semiconductor layer of a second conduction type that is formed on the light absorption layer; and

a semiconductor intermediate layer that is interposed between the buffer layer and the light absorption layer, and has a forbidden bandwidth within a range lying between the forbidden bandwidth of the buffer layer and the forbidden bandwidth of the light absorption layer.

Claim 2 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein the impurity concentration of the buffer layer is lower than  $1 \times 10^{17} \text{ cm}^{-3}$ .

U.S. Patent Application Serial No. 10/665,204  
Response filed July 15, 2005  
Reply to OA dated March 23, 2005

Claim 3 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein the semiconductor intermediate layer includes a plurality of semiconductor layers, with forbidden bandwidths being varied stepwise.

Claim 4 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein the semiconductor intermediate layer includes a plurality of semiconductor layers, with forbidden bandwidths being periodically varied.

Claim 5 (Original): The semiconductor light-receiving device as claimed in claim 1, further comprising a composition-graded semiconductor intermediate layer that is interposed between the light absorption layer and the semiconductor layer of the second conduction type, with forbidden bandwidths being varied stepwise.

Claim 6 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein the semiconductor intermediate layer has a lower refractive index than the light absorption layer.

Claim 7 (Original): The semiconductor light-receiving device as claimed in claim 1, further comprising:

U.S. Patent Application Serial No. 10/665,204  
Response filed July 15, 2005  
Reply to OA dated March 23, 2005

a first electrode unit that is electrically connected to the semiconductor layer of the first conduction type, with a first potential being applied to the first electrode unit; and

a second electrode unit that is electrically connected to the semiconductor layer of the second conduction type, a second potential being applied to the second electrode unit.

Claim 8 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein:

the light absorption layer is an InGaAs layer; and

the buffer layer is a  $\text{In}_{1-x}\text{Ga}_x\text{As}_y\text{P}_{1-y}$  ( $0 < x < 1, 0 < y < 1$ ).

Claim 9 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein at least the light absorption layer and the semiconductor layer of the second conduction type form a mesa structure, with light entering the light absorption layer through a side surface of the light absorption layer that is exposed in a process of forming the mesa structure.

Claim 10 (Original): The semiconductor light-receiving device as claimed in claim 9, further comprising a semiconductor optical waveguide path that is formed on the semi-insulating substrate and guides light to the light absorption layer.

U.S. Patent Application Serial No. 10/665,204  
Response filed July 15, 2005  
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Claim 11 (Original): The semiconductor light-receiving device as claimed in claim 1, comprising a PIN-type photodiode.

Claim 12 (Original): The semiconductor light-receiving device as claimed in claim 1, comprising an avalanche photodiode.

Claim 13 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein the semiconductor layer of the second conduction type has a light receiving surface formed thereon.

Claim 14 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein the semi-insulating substrate has a light receiving surface on the bottom surface thereof.

Claim 15 (Original): The semiconductor light-receiving device as claimed in claim 1, wherein the first conduction type is N type.

Claim 16 (Original): A semiconductor light-receiving device comprising:  
a semiconductor substrate of a first conductivity type;  
a buffer layer of the first conductivity type that is formed on the semiconductor substrate and has a lower impurity concentration than the semiconductor substrate;

a light absorption layer that is formed on the buffer layer and generates carriers in accordance with incident light;

a semiconductor layer of a second conductivity type that is formed on the light absorption layer; and

a semiconductor intermediate layer that is interposed between the buffer layer and the light absorption layer, and has a forbidden bandwidth within a range lying between the forbidden bandwidth of the buffer layer and the forbidden bandwidth of the light absorption layer.

Claim 17 (Currently Amended): A semiconductor light-receiving device comprising:

a semi-insulating substrate;

a semiconductor layer of a first conduction type that is formed on the semi-insulating substrate;

a buffer layer of the first conduction type that is formed on the semiconductor layer;

a light absorption layer that is formed on the buffer layer and generates carriers in accordance with incident light;

a semiconductor layer of a second conduction type that is formed on the light absorption layer; and

a high-concentration semiconductor intermediate tunneling layer of the first conduction type that is interposed between the buffer layer and the light absorption layer and has a higher impurity

U.S. Patent Application Serial No. 10/665,204  
Response filed July 15, 2005  
Reply to OA dated March 23, 2005

concentration than the buffer layer, the semiconductor intermediate tunneling layer allowing electrons to pass therethrough to the buffer layer due to a tunnel effect.

Claim 18 (Original): The semiconductor light-receiving device as claimed in claim 17, wherein the impurity concentration of the buffer layer is lower than  $1 \times 10^{17} \text{ cm}^{-3}$ .

Claim 19 (Previously Presented): The semiconductor light-receiving device as claimed in claim 17, wherein the high-concentration semiconductor intermediate tunneling layer has an impurity concentration of  $2 \times 10^{18} \text{ cm}^{-3}$ , and a film thickness of 100 nm or smaller.

Claim 20 (Original): The semiconductor light-receiving device as claimed in claim 17, further comprising a contact layer of the first conduction type that is interposed between the semi-insulating substrate and the buffer layer, the contact layer having a high impurity concentration, with a predetermined potential being supplied to the contact layer.

Claim 21 (Original): The semiconductor light-receiving device as claimed in claim 17, wherein at least the light absorption layer and the semiconductor layer of the second conduction type form a mesa structure, with light entering the light absorption layer through a side surface of the light absorption layer that is exposed in a process of forming the mesa structure.

U.S. Patent Application Serial No. 10/665,204  
Response filed July 15, 2005  
Reply to OA dated March 23, 2005

Claim 22 (Original): The semiconductor light-receiving device as claimed in claim 21, further comprising a semiconductor optical waveguide path that is formed on the semi-insulating substrate and guides light to the light absorption layer.

Claim 23 (Currently Amended): A semiconductor light-receiving device comprising:

- a semiconductor substrate of a first conduction type;
- a buffer layer of the first conduction type that is formed on the semiconductor substrate and has a lower impurity concentration than the semiconductor substrate;
- a light absorption layer that is formed on the buffer layer and generates carriers in accordance with incident light;
- a semiconductor layer of a second conduction type that is formed on the light absorption layer; and
- a high-concentration semiconductor intermediate tunneling layer of the first conduction type that is interposed between the buffer layer and the light absorption layer and has a higher impurity concentration than the buffer layer, the semiconductor intermediate tunneling layer allowing electrons to pass therethrough to the buffer layer due to a tunnel effect.